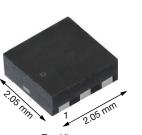
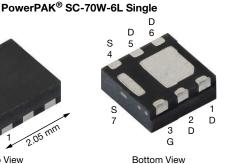
SQA401CEJW

www.vishay.com

Vishay Siliconix

Automotive P-Channel 20 V (D-S) 175 °C MOSFET





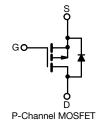
Top View Marking Code: QKXXXX

PRODUCT SUMMARY V_{DS} (V) -20 $R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$ 0.125 $R_{DS(on)}(\Omega)$ at V_{GS} = -2.5 V 0.219 -3.75 I_D (A) Configuration Single

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 gualified
- Wettable flank terminals
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ORDERING INFORMATION			
Package	PowerPAK SC-70W-6L		
Lead (Pb)-free and halogen-free	SQA401CEJW (for detailed order number please see <u>www.vishay.com/doc?79776</u>)		

ABSOLUTE MAXIMUM RATIN	GS (T _C = 25 °C, unless	s otherwise notec	l)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-20	N/	
Gate-source voltage		V _{GS}	± 12	- V	
Continuous drain current ^a	T _C = 25 °C	1	-3.75		
	T _C = 125 °C	I _D	-3.75		
Continuous source current (diode conduction) ^a		IS	-3.75	А	
Pulsed drain current ^b		I _{DM}	-12		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-8		
Single pulse avalanche energy	le pulse avalanche energy		3.2	mJ	
Maximum power dissipation	T _C = 25 °C	- P _D	13.6	W	
	T _C = 125 °C		4.5	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e		-	260	U	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-ambient PCB	mount ^c R _{thJA}	90	°C/W		
Junction-to-case (drain)	R _{thJF}	11	0/10		

Notes

a. Package limited

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR4 material)

See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70W-6L is a leadless package and features wettable flank terminals. d. The end of the lead terminal is plated with tin

Rework conditions: manual soldering with a soldering iron is not recommended for leadless components Not intended for continuous use with positive gate voltage > 3.0 V e.

f.

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For technical questions, contact: automostechsupport@vishay.com

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SQA401CEJW



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = -250 μΑ	-20	-	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-0.6	-1.0	-1.3	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = -20 V		-	-1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -20 V, T _J = 125 °C	-	-	-50	μA
		$V_{GS} = 0 V$	V _{DS} = -20 V, T _J = 175 °C	-	-	-150	1
On-state drain current ^a	I _{D(on)}	$V_{GS} = -4.5 V$	$V_{DS} \ge 5 V$	-8	-	-	Α
		$V_{GS} = -4.5 V$	I _D = -2.4 A	-	0.085	0.125	
Drain-source on-state resistance ^a	P	$V_{GS} = -4.5 V$	I _D = -2.4 A, T _J = 125 °C	-	-	0.175	Ω
Drain-source on-state resistance "	R _{DS(on)}	$V_{GS} = -4.5 V$	I _D = -2.4 A, T _J = 175 °C	-	-	0.200	
		$V_{GS} = -2.5 V$	I _D = -1.8 A	-	0.160	0.219	1
Forward transconductance b	g _{fs}	V _{DS} =	-10 V, I _D = -2.4 A	-	6	-	S
Dynamic ^b							
Input capacitance	C _{iss}			-	265	330	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = -10 V, f = 1 MHz	-	75	94	pF
Reverse transfer capacitance	C _{rss}			-	50	63	
Total gate charge ^c	Qg			-	3.5	5.5	
Gate-source charge ^c	Q _{gs}	$V_{GS} = -4.5 V$	V_{DS} = -10 V, I_{D} = -2.4 A	-	0.9	-	nC
Gate-drain charge ^c	Q _{gd}			-	1.2	-	
Gate resistance	R _g	f = 1 MHz		2.8	5.6	8.4	Ω
Turn-on delay time ^c	t _{d(on)}			-	20	30	
Rise time ^c	t _r	V _{DD} =	$V_{DD} = -10 \text{ V}, \text{ R}_{\text{I}} = 5.21 \Omega$		18	27	ns
Turn-off delay time ^c	t _{d(off)}	$I_D \cong$ -1.9 A, V_{GEN} = -4.5 V, R_g = 1 Ω		-	19	28	
Fall time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Charact	eristics						
Pulsed current ^a	I _{SM}			1	-	-12	А
Forward voltage	V_{SD}	I _F :	= -2 A, V _{GS} = 0	-	-0.8	-1.2	V
Body diode reverse recovery time	t _{rr}			-	22	44	ns
Body diode reverse recovery charge	Q _{rr}	I _F = -1.5 A, di/dt = 100 A/μs		-	12	24	nC
Reverse recovery fall time	t _a			-	9	-	n 0
Reverse recovery rise time	t _b			-	13	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1	-	Α

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

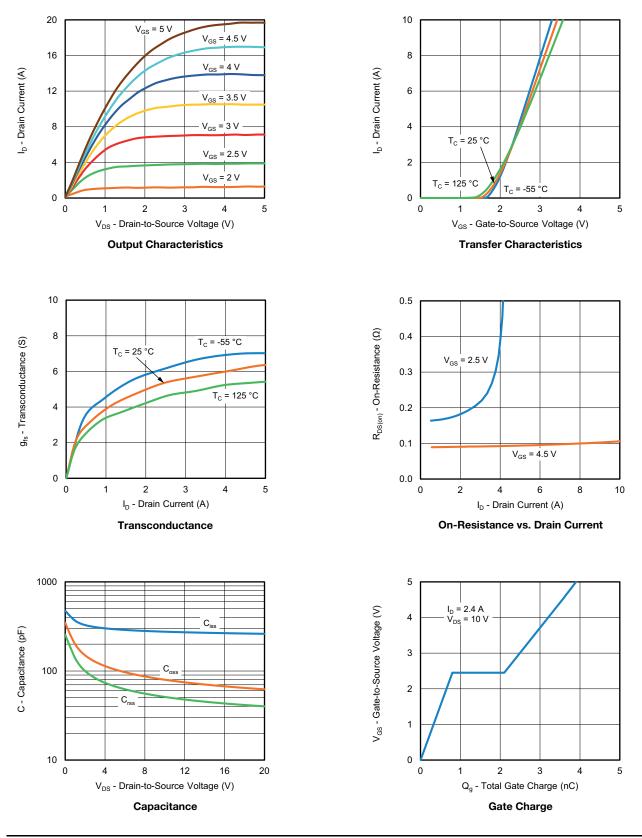
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



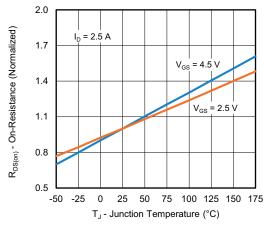
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3 For technical questions, contact: <u>automostechsupport@vishay.com</u>

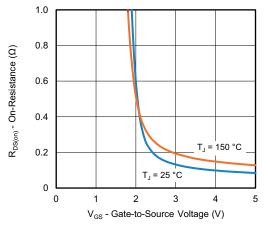


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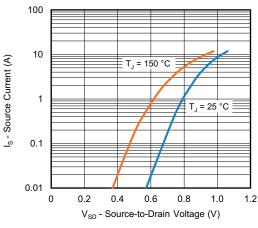
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



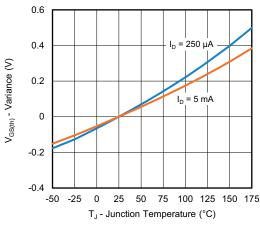
On-Resistance vs. Junction Temperature



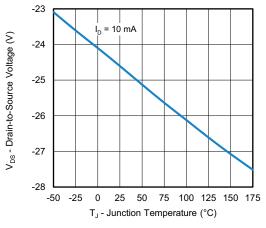
On-Resistance vs. Gate-to-Source Voltage



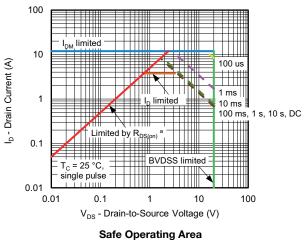
Source-Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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Note

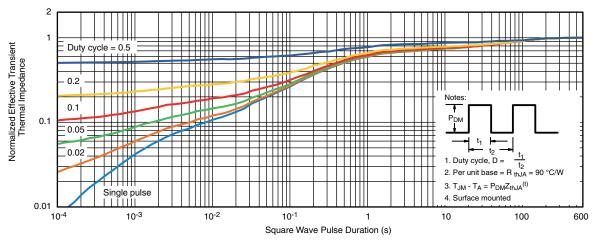
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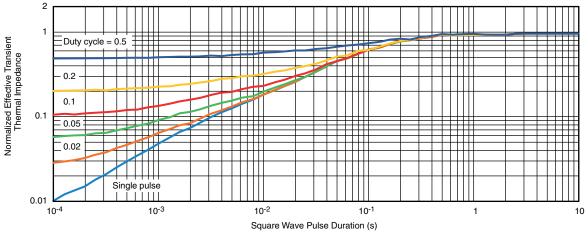


Vishay Siliconix

THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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